

TOSHIBA Diode Silicon Epitaxial Shottlky Barriere Type

1SS404

High Voltage Switching Applications

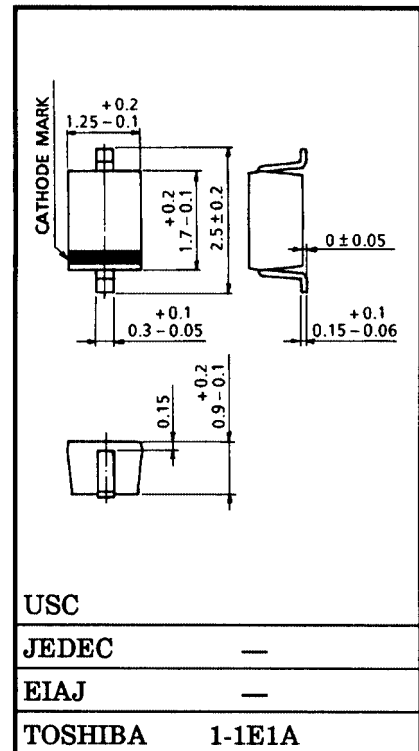
- Tow-pin small packages are suitable for higher mounting densities
- Excellent in Forward Current and Forward Voltage Characteristics : $V_F(3) = 0.8\text{ V (typ.)}$
- Fast Reverse Recovery Time: $I_R = 50\ \mu\text{A (max)}$
- Small Total Capacitance: $C_T = 46\ \text{pF (typ.)}$

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	25	V
Reverse voltage	V_R	20	V
Maximum (peak) forward current	I_{FM}	700	mA
Average forward current	I_O	300	mA
Power dissipation	P	200 (Note)	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 125	$^\circ\text{C}$

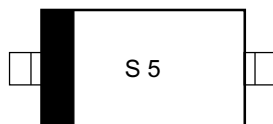
Note: When mounted on a glass epoxy board PCB: 20 mm × 20 mm, with copper pad 4 mm × 4 mm.

Unit in mm

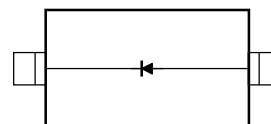


Weight : 0.004g

Marking



Equivalent Circuit (top view)



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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F (1)	I _F = 1 mA	—	0.16	—	V
	V _F (2)	I _F = 10 mA	—	0.22	—	
	V _F (3)	I _F = 300 mA	—	0.38	0.45	
Reverse current	I _R	V _R = 20 V	—	—	50	μA
Total capacitance	C _T	V _R = 0, f = 1 MHz	—	46	—	pF

